

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- A14
1. (Currently amended): A method of fabricating a semiconductor device, the method comprising:
 - depositing a layer to a predetermined thickness on a wafer;
 - planarizing the deposited layer to remove a portion of the deposited layer, the resulting planarized layer comprising a uniform region of uniform thickness extending along a wafer surface ~~and nearly to an edge of the wafer~~, and a non-uniform region of non-uniform thickness corresponding to ~~the edge~~ an upper sidewall of the wafer;
 - coating a photoresist layer on the planarized layer;
 - removing a portion of the ~~coated~~ photoresist layer ~~corresponding to~~ coated on ~~an edge region~~ portion of the uniform region of the planarized layer and on the non-uniform region of the planarized layer ~~wafer~~, thereby exposing at least the non-uniform region of the planarized layer;
 - etching at least the exposed non-uniform region of the planarized layer; and
 - stripping a remaining portion of the coated photoresist layer on the planarized layer, thereby forming a pattern layer comprising a portion of the uniform region of the planarized layer.
 2. (Original): The method of claim 1, wherein the planarizing comprises a chemical mechanical polishing (CMP) process.
 3. (Original): The method of claim 1, wherein the coating of the photoresist

layer continues until the photoresist layer has a thickness of approximately 5000-15000 Å.

4. (Original): The method of claim 1, wherein the etching comprises a wet etching process.

5. (Original): The method of claim 4, wherein the exposing also exposes a portion of the uniform region of the planarized layer.

6. (Original): The method of claim 5, wherein the wet etching also removes the exposed portion of the uniform region of the planarized layer.

7. (Currently amended): A method of fabricating a semiconductor device, the method comprising:

depositing a layer to a predetermined thickness on a wafer, the deposited layer comprising a uniform region of uniform thickness extending along a wafer surface ~~and nearly to an edge of the wafer~~, and a non-uniform region of non-uniform thickness corresponding to ~~the edge~~ an upper sidewall of the wafer;

coating a photoresist layer on the deposited layer;

removing a portion of the ~~coated~~ photoresist layer ~~corresponding to~~ coated on an edge region portion of the uniform region of the deposited layer and on the non-uniform region of the deposited layer ~~wafer~~, thereby exposing at least the non-uniform region of the deposited layer;

etching at least the exposed non-uniform region of the deposited layer;

stripping a remaining portion of the coated photoresist layer on the deposited layer; and

planarizing the uniform region of the deposited layer to thereby forming a pattern

layer comprising the uniform region of the planarized layer.

8. (Original): The method of claim 7, wherein the planarizing comprises a chemical mechanical polishing (CMP) process.

9. (Original): The method of claim 7, wherein the coating of the photoresist layer continues until the photoresist layer has a thickness of approximately 5000-15000 Å.

10. (Original): The method of claim 7, wherein the etching comprises a wet etching process.

11. (Original): The method of claim 10, wherein the exposing also exposes a portion of the uniform region of the deposited layer.

12. (Original): The method of claim 11, wherein the wet etching also removes the exposed portion of the uniform region of the deposited layer.
